

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CMPFJ174
CMPFJ175
CMPFJ176
CMPFJ177

**SURFACE MOUNT
SILICON P-CHANNEL JFET**

SOT-23 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPFJ174 Series types are epoxy molded P-Channel Silicon Junction Field Effect Transistor manufactured in an SOT-23 case, designed for low level amplifier applications.

Marking codes are 6V, 6W, 6X and 6Y respectively.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

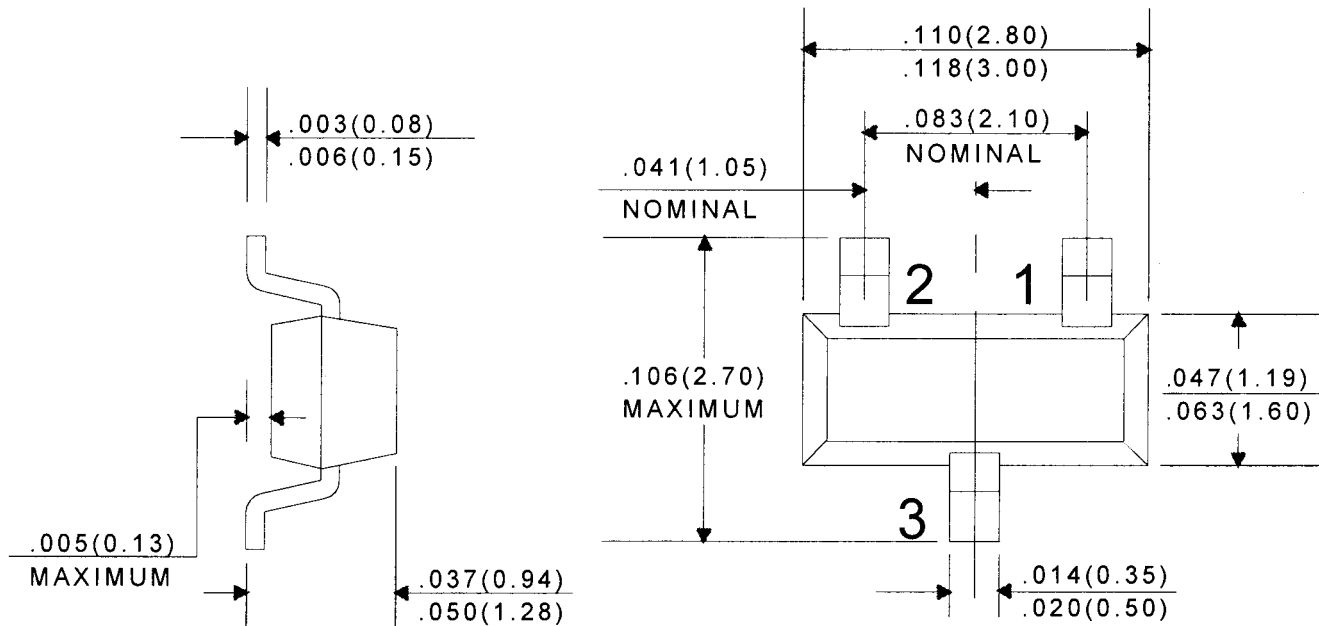
	<u>SYMBOL</u>		<u>UNITS</u>
Gate-Drain Voltage	V_{GD}	30	V
Gate-Source Voltage	V_{GS}	30	V
Gate Current	I_G	50	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	CMPFJ174		CMPFJ175		CMPFJ176		CMPFJ177		<u>UNITS</u>
		<u>MIN</u>	<u>MAX</u>	<u>MIN</u>	<u>MAX</u>	<u>MIN</u>	<u>MAX</u>	<u>MIN</u>	<u>MAX</u>	
I_{GSS}	$V_{GS}=20\text{V}$		1.0		1.0		1.0		1.0	nA
I_{DSS}	$V_{DS}=15\text{V}$	20	100	7.0	60	2.0	25	1.5	20	mA
BV_{GSS}	$I_G=1.0\mu\text{A}$	30		30		30		30		V
$V_{GS(off)}$	$V_{DS}=15\text{V}, I_D=10\text{nA}$	5.0	10	3.0	6.0	1.0	4.0	0.8	2.5	V
$r_{DS(ON)}$	$V_{DS}=0.1\text{V}$		85		125		250		300	Ω

(SEE REVERSE SIDE)

SOT-23 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm)

LEAD CODE:

- 1) DRAIN
- 2) SOURCE
- 3) GATE

MARKING CODE:

- CMPFJ174 - 6V
- CMPFJ175 - 6W
- CMPFJ176 - 6X
- CMPFJ177 - 6Y

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